

isc N-Channel MOSFET Transistor

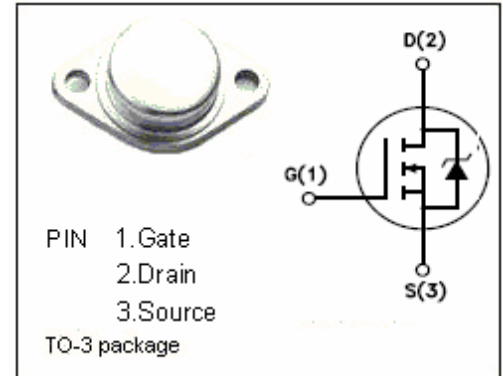
IRF222

DESCRIPTION

- Drain Current  $I_D=4A @ T_C=25^\circ C$
- Drain Source Voltage-  
:  $V_{DSS}= 200V(\text{Min})$
- Static Drain-Source On-Resistance  
:  $R_{DS(on)} = 1.2 \Omega (\text{Max})$
- High Speed Applications

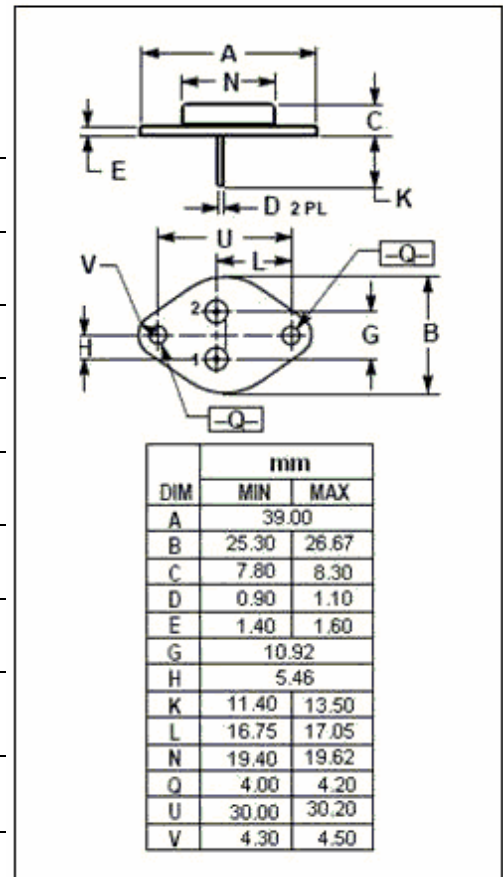
APPLICATIONS

- Switching power supplies



ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ C$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{DSS}$	Drain-Source Voltage ( $V_{GS}=0$ )	200	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Drain Current-continuous@ $T_C=25^\circ C$	4	A
$P_{tot}$	Total Dissipation@ $T_C=25^\circ C$	40	W
$T_j$	Max. Operating Junction Temperature	150	$^\circ C$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ C$



THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance,Junction to Case	3.12	$^\circ C/W$
$R_{th j-a}$	Thermal Resistance,Junction to Ambient	30	$^\circ C/W$

## isc N-Channel Mosfet Transistor

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• ELECTRICAL CHARACTERISTICS ( $T_C=25^\circ\text{C}$ )

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0; I_D=250\mu\text{A}$	200			V
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}; I_D=250\mu\text{A}$	2.0		4.0	V
$R_{DS(ON)}$	Drain-Source On-stage Resistance	$V_{GS}=10\text{V}; I_D=2.5\text{A}$			1.2	$\Omega$
$I_{GSS}$	Gate Source Leakage Current	$V_{GS}=\pm 20\text{V}; V_{DS}=0$			$\pm 100$	nA
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=200\text{V}; V_{GS}=0$			250	$\mu\text{A}$
$V_{SD}$	Diode Forward Voltage	$I_S=4\text{A}; V_{GS}=0$			1.8	V
$C_{iss}$	Input Capacitance	$V_{DS}=25\text{V};$ $V_{GS}=0\text{V};$ $f_T=1\text{MHz}$			600	pF
$C_{rss}$	Reverse Transfer Capacitance				80	
$C_{oss}$	Output Capacitance				300	
$t_r$	Rise Time	$I_D=2.5\text{A};$ $V_{DD}=100\text{V};$ $R_L=50\Omega$			60	ns
$t_{d(on)}$	Turn-on Delay Time				40	
$t_f$	Fall Time				60	
$t_{d(off)}$	Turn-off Delay Time				100	